SSF4N60F

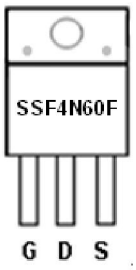
600V N-Channel MOSFET

Main Product Characteristics

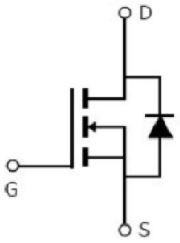
V_{DSS}	600V
R_{DS}(on)	1.9Ω(typ.)
I_D	4A



TO-220F



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150℃ operating temperature
- Lead free product

Description

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V①	4	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V①	2.5	
I_{DM}	Pulsed Drain Current②	16	
P_D @TC = 25°C	Power Dissipation③	33	W
	Linear Derating Factor	0.26	W/°C
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy @ L=27.5mH	220	mJ
I_{AS}	Avalanche Current @ L=27.5mH	4	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

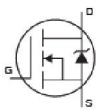
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case③	—	3.79	℃/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ④	—	62	℃/W
	Junction-to-Ambient (PCB mounted, steady-state) ④	—	40	℃/W

Electrical Characteristics @T_A=25℃ unless otherwise specified

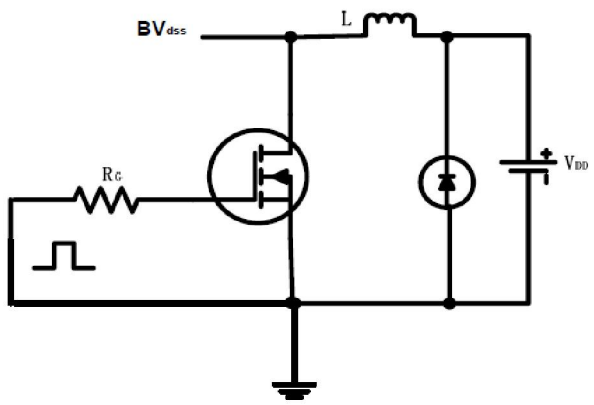
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	600	—	—	V	V_{GS} = 0V, ID = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.9	2.1	Ω	V_{GS}=10V,I_D = 2A
		—	4.63	—		T_J = 125℃
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	V_{DS} = V_{GS}, I_D = 250μA
		—	2.28	—		T_J = 125℃
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} = 600V,V_{GS} = 0V
		—	—	50		T_J = 125℃
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =30V
		—	—	-100		V_{GS} = -30V
Q_g	Total gate charge	—	17.8	—	nC	I_D = 4A,
Q_{gs}	Gate-to-Source charge	—	3.7	—		V_{DS}=480V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	7.1	—		V_{GS} = 10V
$t_{d(on)}$	Turn-on delay time	—	10.9	—	ns	V_{GS}=10V, VDS=300V,
t_r	Rise time	—	16.3	—		R_L=75Ω,
$t_{d(off)}$	Turn-Off delay time	—	40.0	—		R_{GEN}=25Ω
t_f	Fall time	—	31.8	—		ID=4A
C_{iss}	Input capacitance	—	537	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	59	—		V_{DS} = 25V
C_{rss}	Reverse transfer capacitance	—	6	—		f = 1MHz

Source-Drain Ratings and Characteristics

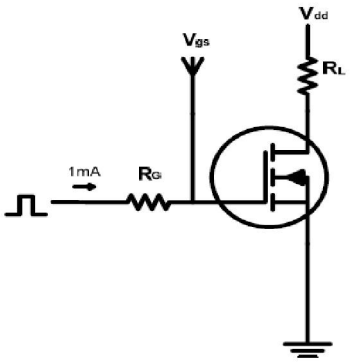
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	4	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	16	A	
V_{SD}	Diode Forward Voltage	—	0.87	1.3	V	I_S=4A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	—	311.6	—	ns	T_J = 25°C, I_F =4A, di/dt = 100A/μs
Q_{rr}	Reverse Recovery Charge	—	2476	—	nC	

Test Circuits and Waveforms

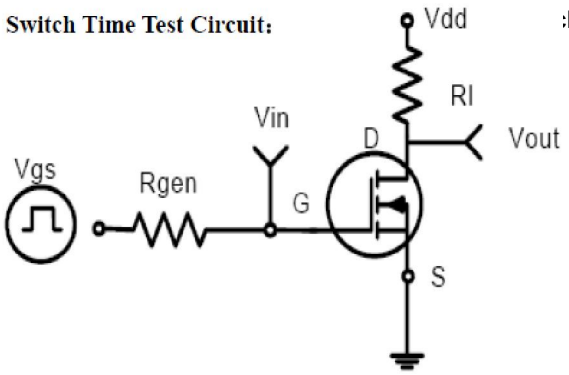
EAS test circuits:



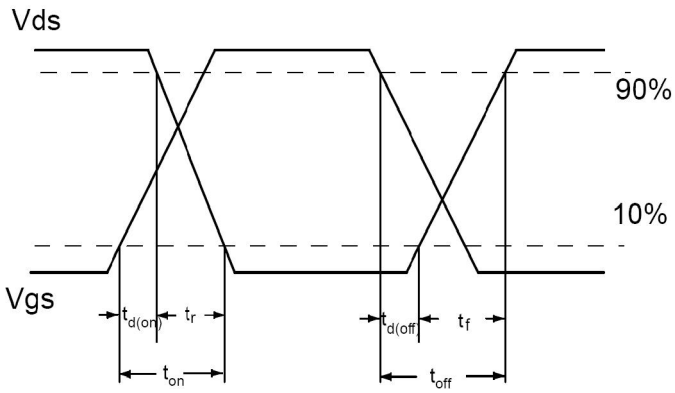
Gate charge test circuit:



Switch Time Test Circuit:



Switch Waveforms:



Notes:

①Calculated continuous current based on maximum allowable junction temperature.

②Repetitive rating; pulse width limited by max. junction temperature.

③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

④The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C

Typical Electrical and Thermal Characteristics

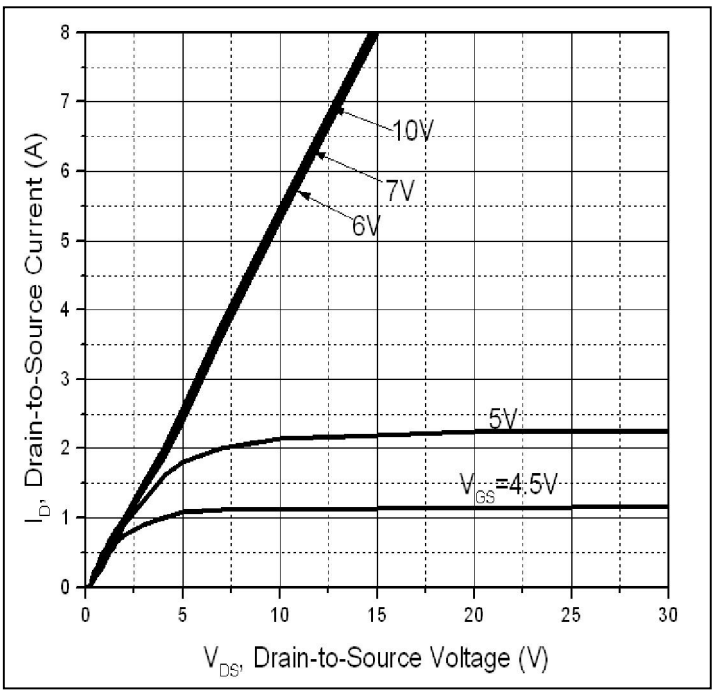


Figure 1: Typical Output Characteristics

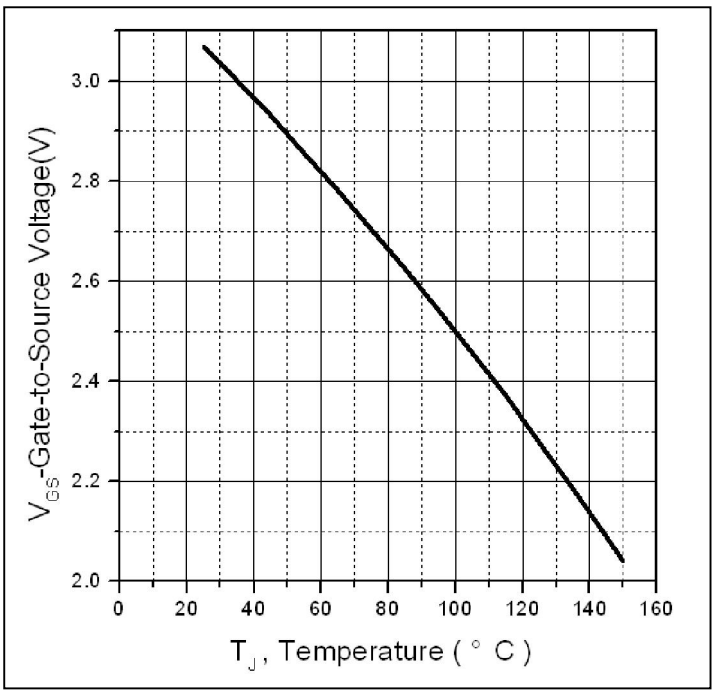


Figure 2. Gate to source cut-off voltage

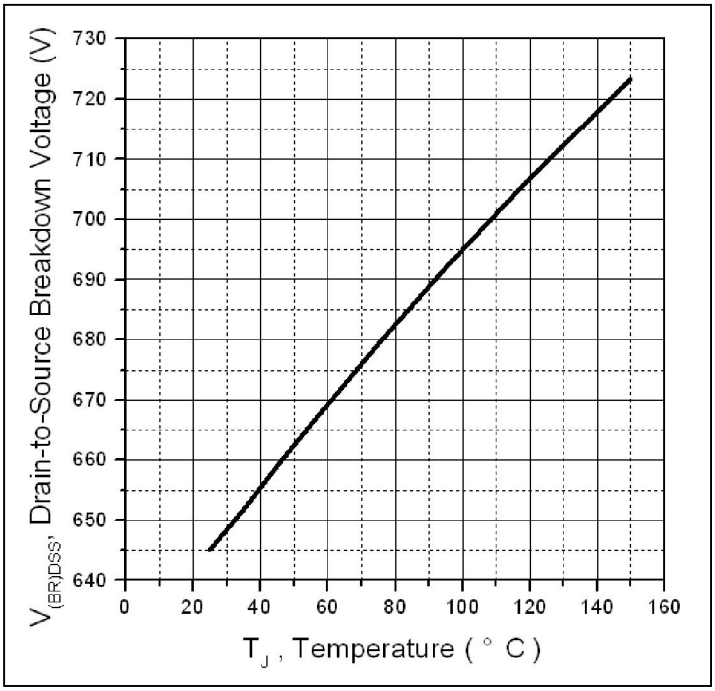


Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature

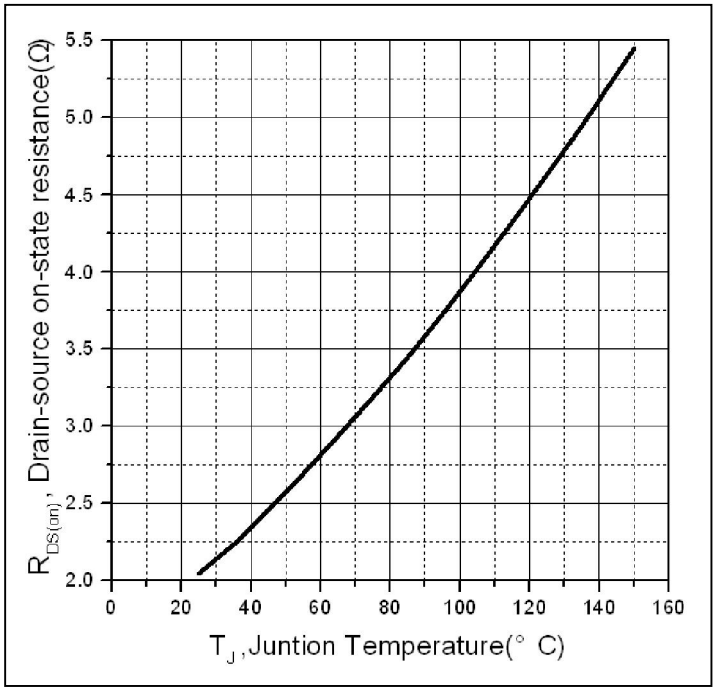


Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical Electrical and Thermal Characteristics

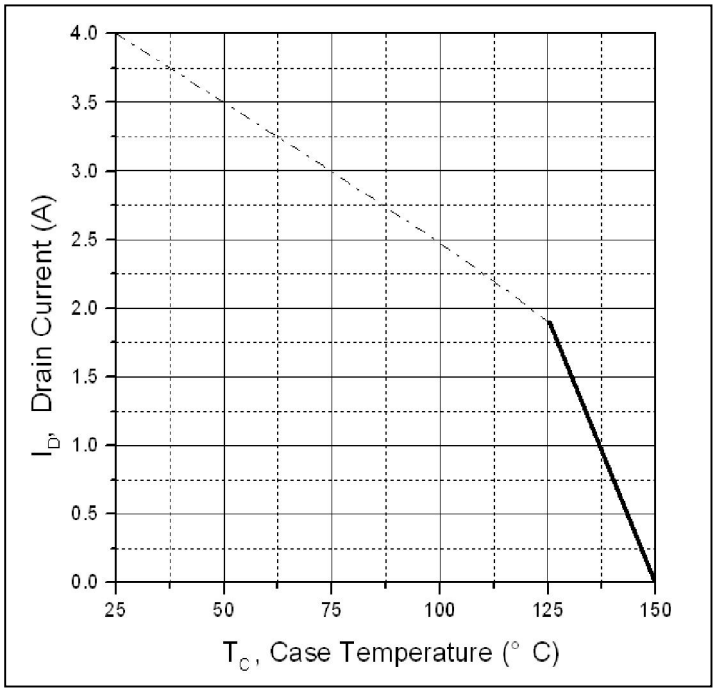


Figure 5. Maximum Drain Current Vs. Case Temperature

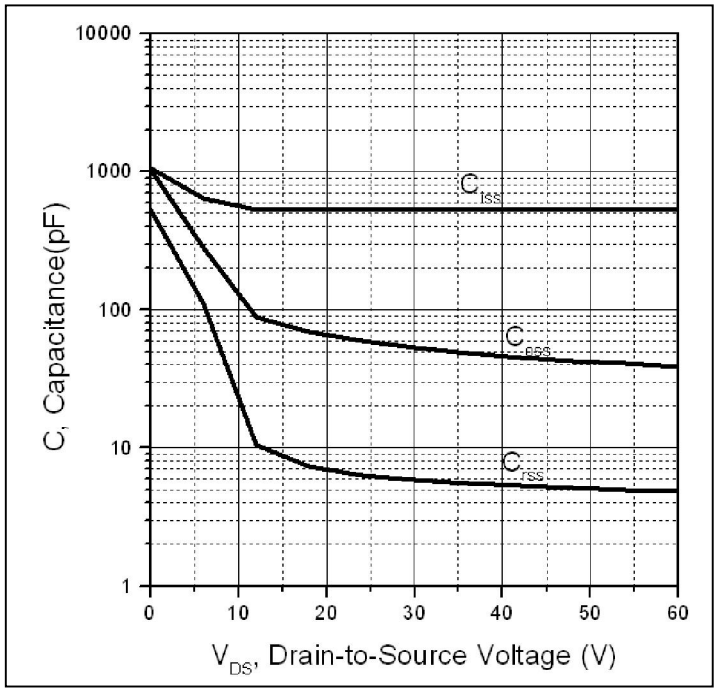


Figure 6.Typical Capacitance Vs. Drain-to-Source Voltage

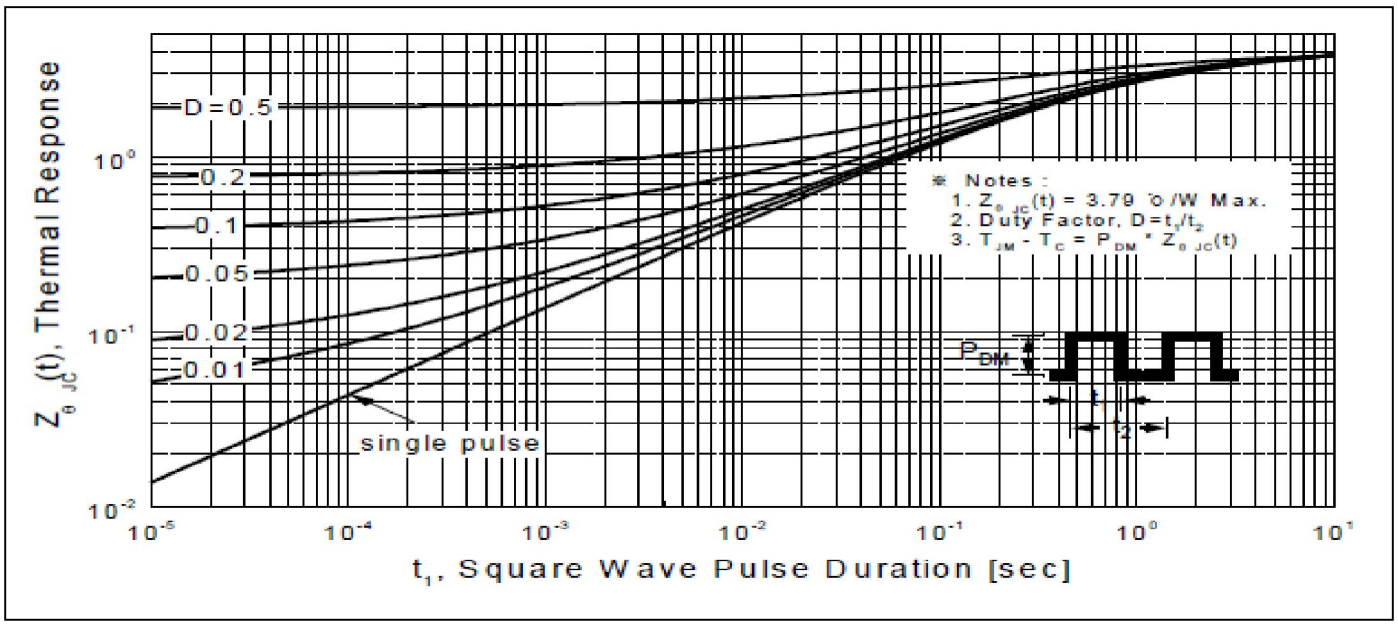
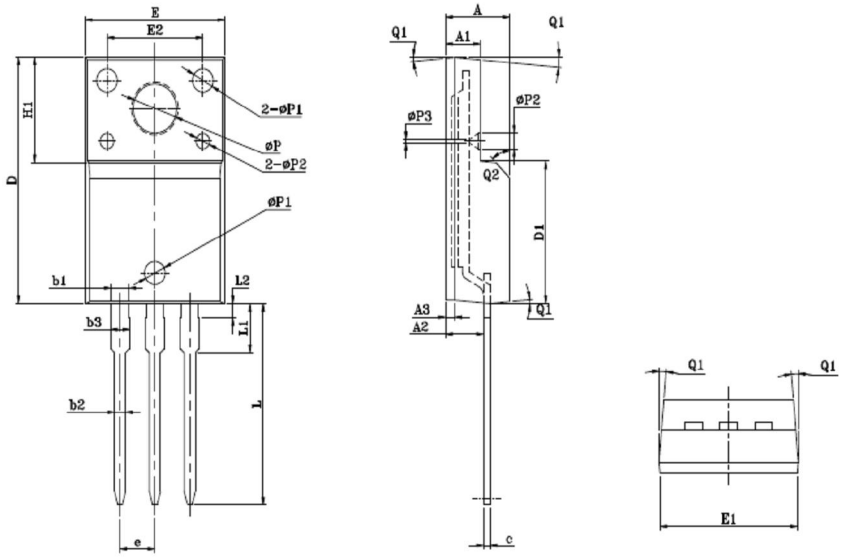


Figure7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data

TO220F PACKAGE OUTLINE DIMENSION_GN



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
E	9.960	10.160	10.360	0.392	0.400	0.408
E1	9.840	10.040	10.240	0.387	0.395	0.403
E2	6.800	7.000	7.200	0.268	0.276	0.283
A	4.600	4.700	4.800	0.181	0.185	0.189
A1	2.440	2.540	2.640	0.096	0.100	0.104
A2	2.660	2.760	2.860	0.105	0.109	0.113
A3	0.600	0.700	0.800	0.024	0.028	0.031
c	-	0.500	-	-	0.020	-
D	15.780	15.870	15.980	0.621	0.625	0.629
D1	8.970	9.170	9.370	0.353	0.361	0.369
H1	6.500	6.700	6.800	0.256	0.264	0.268
e		2.54BSC			0.10BSC	
ΦP	3.080	3.180	3.280	0.121	0.125	0.129
ΦP1	1.400	1.500	1.600	0.055	0.059	0.063
ΦP2	0.900	1.000	1.100	0.035	0.039	0.043
ΦP3	0.100	0.200	0.300	0.004	0.008	0.012
L	12.780	12.980	13.180	0.503	0.511	0.519
L1	2.970	3.170	3.370	0.117	0.125	0.133
L2	0.830	0.930	1.030	0.033	0.037	0.041
Q1	3°	5°	7°	3°	5°	7°
Q2	43°	45°	47°	43°	45°	47°
b1	1.180	1.280	1.380	0.046	0.050	0.054
b2	0.760	0.800	0.840	0.030	0.031	0.033
b3	-	-	1.420	-	-	0.056

Ordering and Marking Information

Device Marking: SSF4N60F

Package (Available)

TO220F

Operating Temperature Range

C : -55 to 150 ºC

Devices per Unit

Package Type	Units/ Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO220F	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T_j=125℃ to 150℃ @ 80% of Max V_{DSS}/V_{CES}/VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T_j=150℃ @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices